



### **Index Guided AlGaInP Laser Diode**

**Package Dimensions** 

### Overview

DL-3149-054 is 670 nm (Typ.) index guided AlGaInP laser diode with low threshold current and high operating temperature. The low threshold current and high operating temperature are achieved by the use of a strained multiple quantum well active layer. DL-3149-054 is suitable for applications such as bar-code scanners, laser pointers and other optical information systems.

#### **Features**

·Short wavelength : 670 nm (Typ.) •High operating temperature : 5 mW at 60°C •Low threshold current : Ith = 30 mA (Typ.)

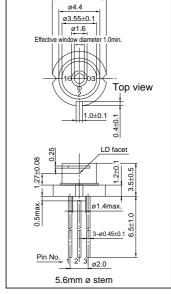
•Small package : 5.6 mmØ

### Absolute Maximum Ratings at Tc=25°C

Parameter		Symbol	Ratings	Unit	
Light Output		Po	5	mW	
Reverse Voltage	Laser PIN	VR	2 30	V	
Operating Temperature		Topr	-10 to +60	°C	
Storage Temperature		Tstg	-40 to +85	°C	

### Electrical and Optical Characteristics at Tc=25°C

# 0 ø5.6-0.025 Tolerance : ±0.2 Unit ø4.4 ø3.55±0.1 ø1.6 Top view



# power supply system

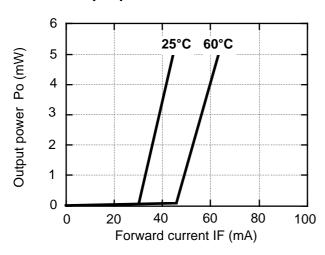
**Electrical Connection** 

Parai	meter	Symbol	Condition	Min.	Тур.	Max.	Unit
Threshol	d Current	Ith	CW	-	30	50	mA
Operating	g Current	Iop	Po=5mW	-	45	60	mA
Operating	g Voltage	Vop	Po=5mW	-	2.3	2.6	V
Lasing W	avelength	λp	Po=5mW	660	670	680	nm
Beam **)	Perpendicular	$ heta oldsymbol{\perp}$	Po=5mW	25	33	40	deg.
Divergence	Parallel	heta //	Po=5mW	6	8	10	deg.
Off Axis	Perpendicular	$\Delta  heta \perp$	_	-	-	±3	deg.
Angle	Parallel	$\Delta  heta$ //	-	-	-	±3	deg.
Differential	l Efficiency	dPo/dIop	-	0.15	0.3	-	mW/mA
Monitoring O	utput Current	Im	Po=5mW	0.4	1.2	2.0	mA
Astign	natism	As	Po=5mW	_	8	_	μm

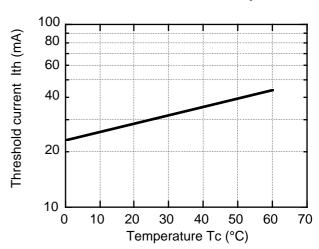
<sup>\*\*)</sup> Full angle at half maximum note: The above product specifications are subject to change without notice.

### **Characteristics**

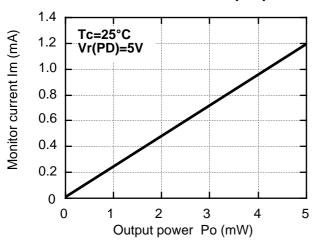
### Output power vs. Forward current



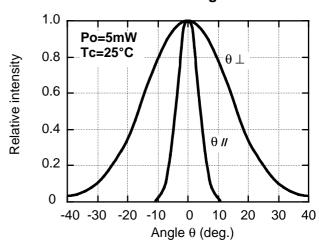
### Threshold current vs. Temperature



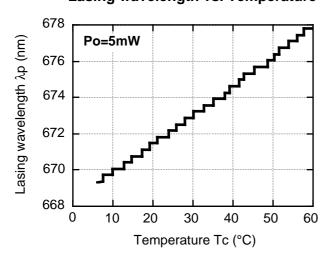
Monitor current vs. Output power



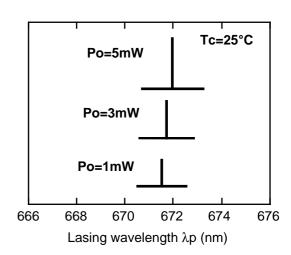
Beam divergence



### Lasing wavelength vs. Temperature



Output power vs. Lasing wavelength



Relative intensity



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## Precautionary instructions in handling gallium arsenic products

Special precautions must be taken in handling this product because it contains, gallium arsenic, which is designated as a toxic substance by law. Be sure to adhere strictly to all applicable laws and regulations enacted for this substance, particularly when it comes to disposal.

Manufactured by; Tottori SANYO Electric Co., Ltd.

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